

### **Amendments to the Claims**

This listing of claims will replace all prior versions, and listings of claims in the application:

#### **Listing of Claims:**

Claim 1 (Currently Amended): A semiconductor device comprising:

a substrate;

an electrode pad formed over the substrate;

a seal layer which seals a semiconductor element formed on the substrate,

wherein a side surface of the seal layer is positioned inside of a side surface of the substrate, the electrode pad is formed next to the side surface of the seal layer, and the side surface of the substrate and the side surface of the seal layer are located along a substrate grid line.

Claim 2 (Original): The semiconductor device according to claim 1, wherein the side surface of the seal layer has a cut cross-section formed by grinding, and the side surface of the substrate has a cut cross-section formed by applying laser light to the substrate.

Claim 3 (Original): The semiconductor device according to claim 1, wherein the side surface of the seal layer is positioned inside of the side surface of the substrate within a

range of 5 $\mu$ m to 100 $\mu$ m.

Claim 4 (Currently Amended): The semiconductor device according to claim 1 ~~claim 1~~, wherein the substrate is a silicon substrate or a sapphire substrate ~~[[whose]]~~ having a surface [[is]] formed with a silicon thin film.

Claim 5 (Currently Amended): A semiconductor device comprising:

a substrate;

an electrode pad formed over the substrate;

a sealing resin sealing a semiconductor element formed on the substrate,

wherein a side surface of the sealing resin is positioned inside of a side surface of the substrate, the electrode pad is formed next to the side surface of the sealing resin, and the side surface of the substrate and the side surface of the sealing resin are located along a substrate grid line.

Claim 6 (Original): The semiconductor device according to claim 5, wherein the side surface of the sealing resin has a cut cross-section formed by grinding, and the side surface of the substrate has a cut cross-section formed by applying laser light to the substrate.

Claim 7 (Original): The semiconductor device according to claim 5, wherein the side

surface of the sealing resin is positioned inside of the side surface of the substrate within a range of 5 $\mu$ m to 100 $\mu$ m.

Claim 8 (Currently Amended): The semiconductor device according to ~~claim 5~~ claim 5, wherein the substrate is a silicon substrate or a sapphire substrate having a ~~[[whose]]~~ surface ~~[[is]]~~ formed with a silicon thin film.

Claim 9 (Currently Amended): A semiconductor device comprising:

a substrate which has a main surface formed with a circuit element;  
an electrode pad formed over the main surface of the substrate and which is electrically connected to the circuit element;

a wiring which is formed over the main surface and which is electrically connected to the electrode pad ~~circuit element~~;

a sealing resin which covers the main surface of the substrate and the wiring; and

an external terminal which is electrically connected to the wiring and which is exposed from a surface of the sealing resin,

wherein an edge of the sealing resin is formed inside an edge of the substrate, the electrode pad is formed next to the edge of the sealing resin, and the edge of the substrate and the edge of the sealing resin are located along a substrate grid line.

Claim 10 (Original): The semiconductor device according to claim 9, wherein a side surface of the sealing resin has a cut cross-section formed by grinding, and a side surface of the substrate has a cut cross-section formed by applying laser light to the substrate.

Claim 11 (Currently Amended): The semiconductor device according to claim 9, wherein ~~[[the]]~~ a side surface of the sealing resin is positioned inside of a side surface within a range of 5 $\mu$ m to 100 $\mu$ m.

Claim 12 (Currently Amended): The semiconductor device according to claim 9, wherein the substrate is a silicon substrate or a sapphire substrate having a ~~[[whose]]~~ surface ~~[[is]]~~ formed with a silicon thin film.